

12A, 60V, 0.150 Ohm, N-Channel Power MOSFETs

These are N-Channel enhancement mode silicon gate power field effect transistors. They are advanced power MOSFETs designed, tested, and guaranteed to withstand a specified level of energy in the breakdown avalanche mode of operation. All of these power MOSFETs are designed for applications such as switching regulators, switching convertors, motor drivers, relay drivers, and drivers for high power bipolar switching transistors requiring high speed and low gate drive power. These types can be operated directly from integrated circuits.

Formerly developmental type TA49082.

Ordering Information

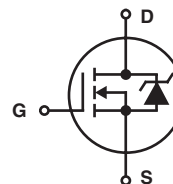
PART NUMBER	PACKAGE	BRAND
RFD3055	TO-251AA	FD3055
RFD3055SM	TO-252AA	FD3055
RFP3055	TO-220AB	FP3055

NOTE: When ordering, use the entire part number. Add the suffix 9A, to obtain the TO-252AA variant in tape and reel, i.e. RFD3055SM9A.

Features

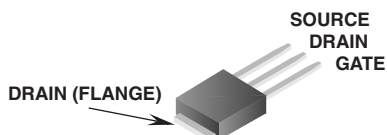
- 12A, 60V
- $r_{DS(ON)} = 0.150\Omega$
- Temperature Compensating PSPICE[®] Model
- Peak Current vs Pulse Width Curve
- UIS Rating Curve
- 175°C Operating Temperature
- Related Literature
 - TB334 "Guidelines for Soldering Surface Mount Components to PC Boards"

Symbol

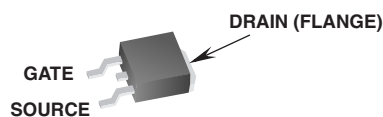


Packaging

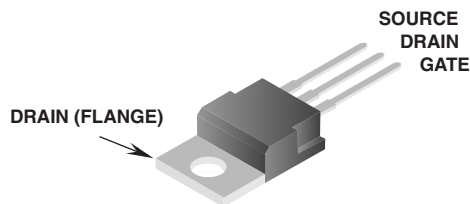
JEDEC TO-251AA



JEDEC TO-252AA



JEDEC TO-220AB



RFD3055, RFD3055SM, RFP3055

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

	RFD3055, RFD3055SM, RFP3055	UNITS
Drain to Source Voltage (Note 1)	V_{DSS}	60 V
Drain to Gate Voltage ($R_{GS} = 20\text{K}\Omega$) (Note 1)	V_{DGR}	60 V
Gate to Source Voltage	V_{GS}	± 20 V
Continuous Drain Current	I_D	12 A
Pulsed Drain Current (Note 3)	I_{DM}	Refer to Peak Current Curve
Single Pulse Avalanche Rating (Figures 14, 15)	I_{AS}	Refer to UIS Curve
Power Dissipation	P_D	53 W
Linear Derating Factor		0.357 $\text{W}/^\circ\text{C}$
Operating and Storage Temperature	T_J, T_{STG}	-55 to 175 $^\circ\text{C}$
Maximum Temperature for Soldering		
Leads at 0.063in (1.6mm) from Case for 10s.	T_L	300 $^\circ\text{C}$
Package Body for 10s, See Techbrief 334	T_{pkg}	260 $^\circ\text{C}$

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

- $T_J = 25^\circ\text{C}$ to 150°C .

Electrical Specifications $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Drain to Source Breakdown Voltage	BV_{DSS}	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$ (Figure 11)	60	-	-	V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$ (Figure 10)	2	-	4	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = \text{Rated } BV_{DSS}, V_{GS} = 0\text{V}$	-	-	1	μA
		$T_C = 125^\circ\text{C}, V_{DS} = 0.8 \times \text{Rated } BV_{DSS}$	-	-	25	μA
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20\text{V}$	-	-	100	nA
Drain to Source On Resistance	$r_{DS(ON)}$	$I_D = 12\text{A}, V_{GS} = 10\text{V}$ (Figure 9) (Note 2)	-	-	0.150	Ω
Turn-On Time	t_{ON}	$V_{DD} = 30\text{V}, I_D = 12\text{A}$ $R_L = 2.5\Omega, V_{GS} = +10\text{V}$ $R_G = 10\Omega$ (Figure 13)	-	-	40	ns
Turn-On Delay Time	$t_{d(ON)}$		-	7	-	ns
Rise Time	t_r		-	21	-	ns
Turn-Off Delay Time	$t_{d(OFF)}$		-	16	-	ns
Fall Time	t_f		-	10	-	ns
Turn-Off Time	t_{OFF}		-	-	40	ns
Total Gate Charge	$Q_{g(TOT)}$	$V_{GS} = 0$ to 20V	-	19	23	nC
Gate Charge at 10V	$Q_{g(10)}$	$V_{GS} = 0$ to 10V				
Threshold Gate Charge	$Q_{g(TH)}$	$V_{GS} = 0$ to 2V				
Input Capacitance	C_{ISS}	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V},$ $f = 1\text{MHz}$ (Figure 12)	-	300	-	pF
Output Capacitance	C_{OSS}		-	100	-	pF
Reverse Transfer Capacitance	C_{RSS}		-	30	-	pF
Thermal Resistance Junction to Case	$R_{\theta JC}$		-	-	2.8	$^\circ\text{C}/\text{W}$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	TO-251 and TO-252	-	-	100	$^\circ\text{C}/\text{W}$
		TO-220	-	-	62.5	$^\circ\text{C}/\text{W}$

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage	V_{SD}	$I_{SD} = 12\text{A}$	-	-	1.5	V
Reverse Recovery Time	t_{rr}	$I_{SD} = 12\text{A}, dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	100	ns

NOTES:

- Pulse Test: Pulse Width $\leq 300\text{ms}$, Duty Cycle $\leq 2\%$.
- Repetitive Rating: Pulse Width limited by max junction temperature. See Transient Thermal Impedance Curve (Figure 3) and Peak Current Capability Curve (Figure 5).

Typical Performance Curves Unless Otherwise Specified

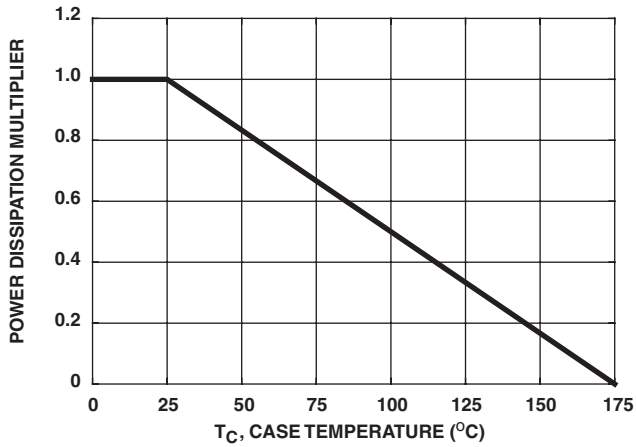


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

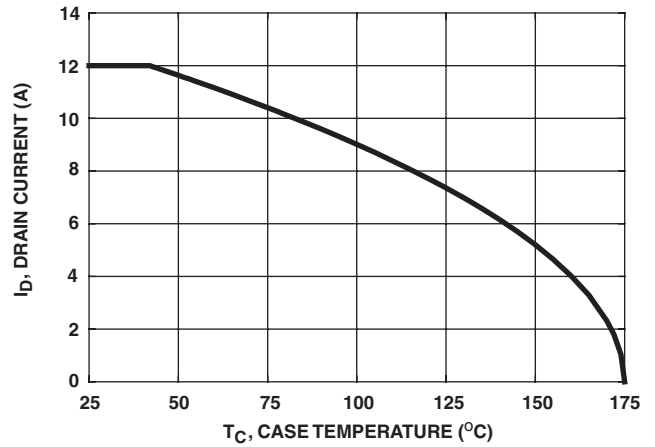


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

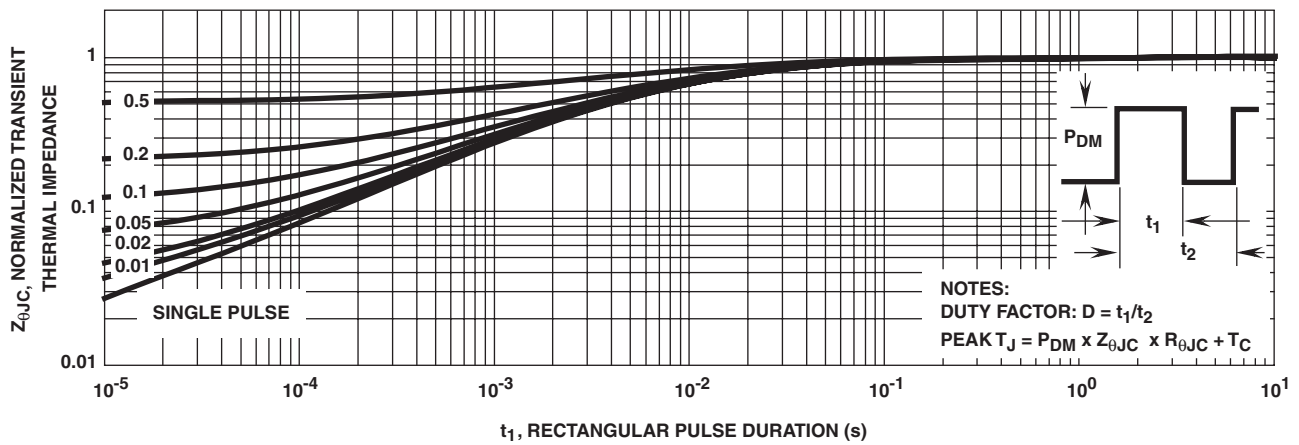


FIGURE 3. NORMALIZED MAXIMUM TRANSIENT THERMAL IMPEDANCE

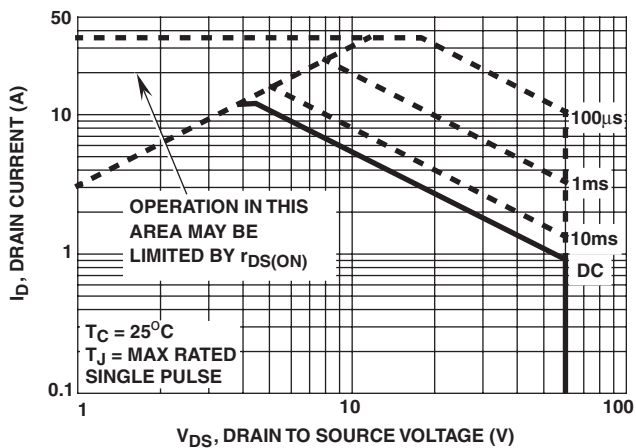


FIGURE 4. FORWARD BIAS SAFE OPERATING AREA

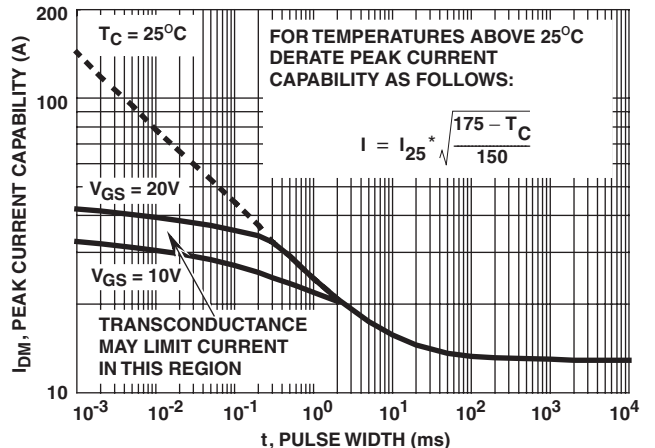


FIGURE 5. PEAK CURRENT CAPABILITY